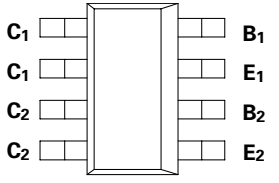
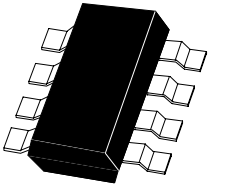
SM-8 DUAL PNP MEDIUM POWER TRANSISTORS

ISSUE 1 - JULY 1999

ZDT795A



PARTMARKING DETAIL – T795A



SM-8
(8 LEAD SOT223)

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-140	V
Collector-Emitter Voltage	V_{CEO}	-140	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-1	A
Continuous Collector Current	I_C	-0.5	A
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	VALUE	UNIT
Total Power Dissipation at T_{amb} = 25°C* Any single die "on" Both die "on" equally	P_{tot}	 2.25 2.75	 W W
Derate above 25°C* Any single die "on" Both die "on" equally		 18 22	 mW/ °C mW/ °C
Thermal Resistance - Junction to Ambient* Any single die "on" Both die "on" equally		 55.6 45.5	 °C/ W °C/ W

* The power which can be dissipated assuming the device is mounted in a typical manner on a PCB with copper equal to 2 inches square.

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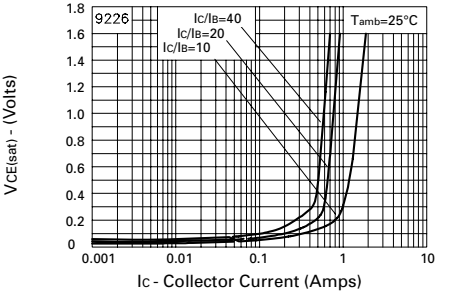
ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-140			V	I_C=-100μA, I_E=0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-140			V	I_C=-10mA, I_B=0*
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	I_E=-100μA, I_C=0
Collector Cutoff Current	I_{CBO}			-0.1	μA	V_{CB}=-100V
Emitter Cutoff Current	I_{EBO}			-0.1	μA	V_{EB}=-4V, I_E=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.3 -0.3 -0.25	V V V	I_C=-100mA, I_B=-1mA* I_C=-200mA, I_B=-5mA* I_C=-500mA, I_B=-50mA*
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-0.95	V	I_C=-500mA, I_B=-50mA*
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.75		V	I_C=-500mA, V_{CE}=-2V*
Static Forward Current Transfer Ratio	h_{FE}	300 250 100		800		I_C=-10mA, V_{CE}=-2V* I_C=-200mA, V_{CE}=-2V* I_C=-300mA, V_{CE}=-2V*
Transition Frequency	f_T	100			MHz	I_C=-50mA, V_{CE}=-5V f=50MHz
Output Capacitance	C_{obo}		15		pF	V_{CB}=-10V f=1MHz
Switching Times	t_{on}		100		ns	I_C=-100mA, V_{CC}=-50V I_{B1}=I_{B2}=-10mA
	t_{off}		1900		ns	

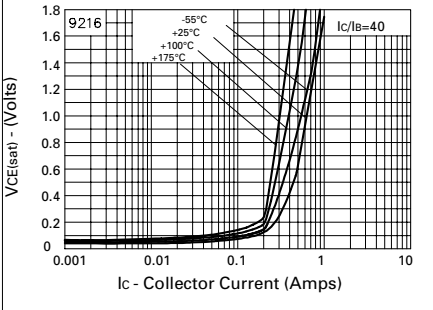
*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤ 2%

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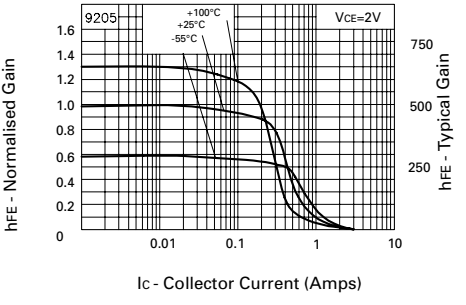
TYPICAL CHARACTERISTICS



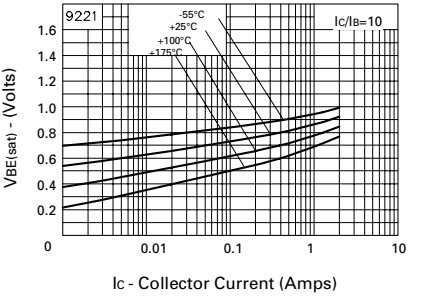
VCE(sat) v IC



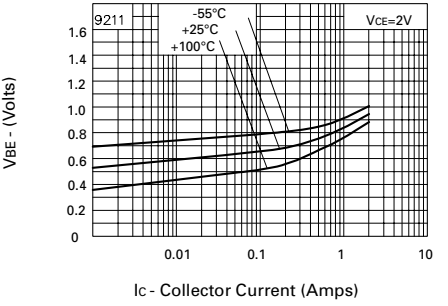
VCE(sat) v IC



hFE v IC



VBE(sat) v IC



VBE(on) v IC